

MAINTENANCE MANUAL 136-174 MHz, 110 WATT POWER AMPLIFIER 19D902797G1

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DESCRIPTION

The VHF Power Amplifier Assembly is a wide band RF power amplifier operating over the entire 136 to 174 MHz range without tuning or band splitting. Its main function is to amplify the 10 mW FM signal from the Transmitter Synthesizer to the rated RF output of 110 watts at the antenna port. The output of the Power Amplifier Assembly is adjustable from 65 to 135 watts at the PA output J104. This corresponds to a rated RF output of 55 to 110 watts at the antenna.

The assembly consists of a printed wiring board (A1) and associated components, including a power module and three RF power transistors, mounted to the heat sink assembly. The printed wiring board (A1) contains both the power

amplifier circuitry (100 series components) and the power control circuitry (200 series components).

Unfiltered supply voltage, A+, for the power amplifier circuits enters the assembly via feedthrough capacitor, C1. Power cable W4 routes the A+ from CI to J103 on the PWB. Filtered A+ voltage for the power control circuit enters the assembly via control cable W13 which connects to the PWB at J201.

The Power Control circuitry sets the output power level by adjusting the PA Power Set level. It keeps the output power constant despite variations in input power, power amplifier gain, or temperature through the use of a feedback control loop in the PA assembly.



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Printed in U.S.A.

TABLE 1 - GENERA	L SPECIFICATIONS
ITEM	SPECIFICATION
FREQUENCY	136 MHz 174 MHz
OUTPUT POWER	65 watts - 135 watts (into Low Pass Filter)
INPUT POWER (RF)	10 mW min. into 2:1 VSWR
TEMPERATURE RANGE	30°C TO + 60°C (Ambient air)
SUPPLY VOLTAGE	13.4 Vdc
CURRENT	29 Amps max. (25 A typical @ 135W, 13.4V)
DUTY CYCLE	Continous
STABILITY	Stable into 3:1 VSWR; all temp. ,voltage, freq. 65 watts - 135 watts
RUGGEDNESS AT HIGH VSWR	No damage into open or short load.

CIRCUIT ANALYSIS

POWER AMPLIFIER

The power amplifier section of the PA Board consists of an Exciter, a Low Level Amplifier, a Driver, and the Power Amplifier Finals. All these gain stages have an input and output impedance of 50 ohms. Figure 1 is a block diagram showing the signal flow within the Power Amplifier Assembly.

Exciter (UIOI)

The Exciter stage uses a broadband silicon monolithic microwave integrated circuit (MMIC) amplifier. The signal from transmitter synthesizer, typically 10 dBm (10 mW), is input to the Exciter through a 10 dB resistive pad (R100R102). The Exciter amplifies the resulting 0 dBm (1 mW) signal to 20 dBm (100 mW). Following the Exciter is a 3 dB resistive pad (R104R106). This attenuatorreduces the MMIC output power to 17 dBm (50 mW).

The MMIC requires a 5 volt supply source. The 8 volt regulator (U100) provides the 5 volts to the MMIC via a dropping resistor R103.

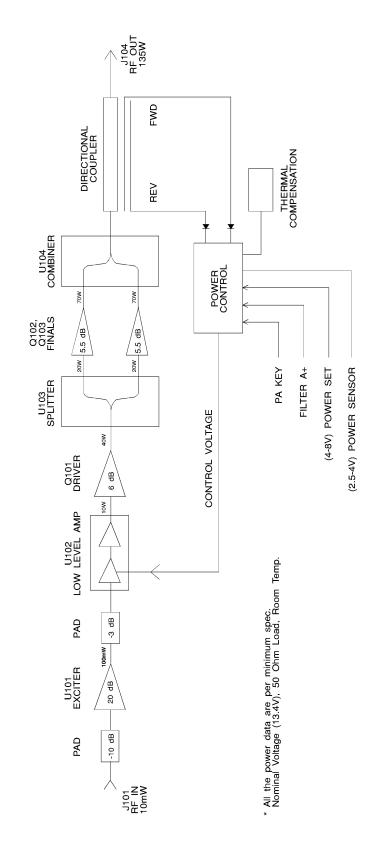
Low Level Amplifier (U1O2)

The Low Level Amplifier (LLA) stage uses a 50 ohm thick film RF Power Module to amplify and control of the output power. Internally, the module is a two stage amplifier. The power control circuitry controls the gain of the first stage by varying the collector voltage of Q203. The second stage gain remains constant with A + providing the DC supply voltage.

The signal from the Exciter stage, typically 17 dBm (50 mW), is input into the LLA. Under maximum Power Set conditions, the LLA amplifies the signal to a typical output level of 40 dBm (10 W).

Driver (Q101)

The driver is a 6 dB RF amplifier. A network consisting of C114C117 and C139 and L103L105 provides interstage impedance matching between U102 and Q101. The signal from the LLA, typically 40 dBm (10 W), is amplified to 46 dBm (40 W). Impedance matching between the driver output and the input to U103 is provided by C145, C148, C152, C153, and L108. The splitter, U103, is a quadrature 90° hybrid coupler. It divides the signal and applies equal power to the two Power Amplifier Finals, Q102 and Q103.



igure 1 - Block Diagram

Power Amplifier Finals (Q102, Q103)

Each of the Power Amplifier Final devices is capable of producing 5.5 dB of gain. The output signal from the Splitter is impedance matched to each of the finals. Under optimum conditions each final amplifies the 43 dBm (20 W) power input signal to 48.45 dBm (70 W) output power. The outputs are then impedance matched to the input of the Combiner, U104. The Combiner is a quadrature 90° hybrid coupler which combines (sums) the output power of the finals. This produces an output power of approximately 51.3 dBm (135 W) which is coupled through C 140 to the directional coupler (part of A1 PWB) and on to the antenna circuits. In addition, the directional coupler samples both forward and reverse power and sends this sample to the Power Control circuitry.

POWER CONTROL

The Power Control circuitry performs three basic functions. It keys and unkeys the PA, sets the PA output power, and protects the PA against adverse conditions.

Keying and Unkeying the PA

To key the PA, the digital controller places 5 volts on the PA key line, J201-2. Zero volts on the PA key line causes the PA to unkey. If the control cable (W13) is disconnected, with nothing actively driving the PA key line, the PA will remain unkeyed.

PA Output Power Set

PA output power is set according to the level of the Power Set line. Four (4) volts on this line will produce minimum power. As the voltage increases toward eight (8) volts, the power will increase to its maximum rated output. The PA output power is initially set for an output of 135 watts at J104. This is done by adjusting R217 while injecting a 10 mW signal at J1 and applying 8 volts to J201-3. After setting the maximum power level, changing the output power is done by varying the voltage applied on the Power Set line.

PA Protection

The power control also protects the PA against over temperature and high VSWR conditions.

An over temperature condition exists when the flange temperature of the final output transistor reaches 80°C. At this point the output power will drop below its set level. The output power will continue to drop such that when the flange temperature reaches 125°C the PA output drops at least 10 dB below its set level.

Reflected power is limited to 25% of the set power. If the output VSWR degrades to worse than 3:1 the forward power will be reduced to limit the reflected power to 25% of the set power. The Power Sensor line indicates when the PA is operating in a cutback condition. If the PA is keyed and the power control is cutting back, the Power Sensor line will

drop to zero (0) volts and the PA alarm light on the station will turn on.

Theory of Operation

Power control of the MASTR III Power Amplifier is accomplished with a feedback control loop. The three possible feedback signals are: representation of forward power, temperature sensitive scaled representation of forward power, or representation of reflected power. These three signals are input to a diode summing junction which selects the largest of the three for use as the feedback.

The stripline directional coupler samples the output power and produces a voltage, Vf, proportional to the forward output power. The power control compares the forward voltage, Vf, to a reference voltage at U201D. The output of U201D controls the current flow thru Q202 and the output of Q203. The collector output of Q203 adjusts the control voltage, Vct1. This control voltage is capable of adjusting the total PA output power since it provides the first stage DC supply to the Low Level Amplifier, U102.

During over temperature operation, a scaled representation of the forward power is maintained constant by varying the control voltage line. Thermal resistor R209 sensing an increase in temperature causes the output of U201A to increase. If the output of U201A becomes larger than the other feedback lines, the output of U201D will begin to decrease. This in turn will cause the output of Q203 to decrease reducing the supply voltage to U102. Since the scaling is a function of temperature the power is reduced as the temperature increases.

Under VSWR cutback operation the reverse voltage, Vr, representative of the reflected output power is held below a threshold by reducing the control voltage as necessary. If Vr increases at U201B beyond the preset threshold an increase at U201D will result. This causes a subsequent reduction in the control voltage to U102. Thus the power control circuit reduces the output power in order to limit the reflected power to 25% of the set power.

Signal Interface

The signal interface to the MASTR III Power Amplifier is supported by a six position feedthrough connector, J201, with the following pinout:

- 1 POWER SENSE
- 2 PA Key
- 3 POWER SET
- 4 NC
- 5 Ground
- 6 13.8 VF

Power Sense

This line indicates when the PA is experiencing adverse conditions. Under normal operation, while the PA is keyed, this line will be proportional to forward power. Minimum power (zero watts) corresponds to 2.5 volts while maximum power corresponds to 4.5 volts. This voltage is not temperature compensated and no effort is made to calibrate this signal to an absolute power level. It is intended to provide a relative indication of forward power and to discriminate between normal and cutback operation.

Zero volts on this line, when the PA is keyed, indicates the forward power is cutback. This power cutback may be due to high reflected power (VSWR) or may be due to high PA temperatures. This fault condition may indicate a problem with the PA or may indicate a system problem external to the Power Amplifier. High VSWR may be due to a poor antenna and high temperature may be due to a blocked cabinet vent. Zero volts on this line, when the PA is keyed, does not indicate zero forward power. Zero volts indicates the PA is protecting itself due to adverse conditions. If the adverse condition, either high VSWR or high temperature is eliminated, the power will return to normal and the PWR SENSOR voltage will rise above 2.5 volts.

PA Key (Interface Connector pin 2)

This line is used to key and unkey the PA. UNKEY = 0 volt and KEY = 5 volts. The driver of this line must be capable of supplying 5 volts at 1.0 mA. The appropriate key sequence requires RF from the transmit synthesizer be input to the PA before the KEY line is energized.

Power Set (Interface Connector pin 3)

This line is used to set the RF Power Output of the PA. Minimum power output equals 4 volts and maximum power output equals 8 volts. The driver of this line must be capable of supplying 8 volts at 1.0 mA.

13.8 VF (Interface Connector pin 6)

This line provides the filtered supply voltage for the Power Control. The driver of this line must be capable of supplying $13.8 \text{ volts} \pm 20\%$ at 100 mA.

TROUBLESHOOTING GUIDE

SYMPTOM	AREAS TO CHECK	INDICATIONS
No Power or low Power at Antenna Port	1. Measure the transmitter output power before the duplexer or antenna switch (for simplex mode).	The presence of power at this port is an indication of a defective duplexer, switch, or cables.
	2. Measuer the transmitter output power before the low pass filter.	The presence of power at this port is an indication of a defective filter or cables.
	3. Measure the transmitter output power before the optional isolator at the PA output port.	The presence of power at this port is an indication of a defective isolator or cables.
2. No power at PA output port and PA ALARM is OFF	1. Station is in receive mode.	
3. No power at PA output port and PA ALARM is ON.	No RF input to PA. Check connection between PA and TX Synthesizer.	TX Synthesizer should deliver a minimum of 10 mW (10 dBm) to the PA.
	2. Check the logic or DC inputs to the PA from the Interface Board through J201.	
	a. J201-2 PA KEY	5 volts during transmit
	b. J201-3 POWER SET	4 volts to 8 volts (4 volts represents zero RF power)
	c. J201-6 13.8 VF	13.8 Vdc ±20%
	3. Defective PA	Replace PA
4. Low power at PA output port and PA ALARM is OFF	Low RF input to PA from TX Synthesizer.	Power should be a minimum of 10 mW (10 dBM).
	2. Check the voltage on J201-3 (POWER SET).	For nominal output power, this voltage should be above 6 volts.
	3. Check the power supply voltage on the collector of Q101, Q102 and Q103.	Voltage should be nominal 13.4 Vdc.
	4. One of the two final PA transistors (Q102 or Q103 is defective.	Replace the defective transistor.
5. Low power at PA output port and PA ALARM is ON.	 Check for over temperature and/or a high VSWR condition due to a mis- match at the output port. 	The power control circuit protects the PA by cutting back the power. In case of a mismatch, refer to symptom 1.

VHF POWER AMPLIFIER VOLTAGE CHART

PARAMETER (50 OHM, -30° TO +60° C)	REFERENCE SYMBOL	READINGS (volts DC)
SUPPLY VOLTAGE	A+	13.4 V ±20%
CONTROL VOLTAGE	Vct 1	0 - 12 V
FORWARD VOLTAGE	Vf	3 - 7 V
REVERSE VOLTAGE	Vr	2 - 6 V
POWER SENSE	J201-1	2.5 - 4 V
PA KEY	J201-2	5 V
POWER SET	J201-3	4 - 8 V
13.8 VF	J201-6	13.8 V ±20%

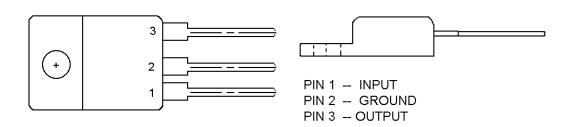
VHF POWER AMPLIFIER TYPICAL VOLTAGE READINGS (50 ohm, room temperature, 13.4 Vdc supply voltage, and 110 watt output)

REFERENCE SYMBOL	@ 136 MHz (volts DC)	@ 150 MHz (volts DC)	@ 162 MHz (volts DC)	@ 174 MHz (volts DC)
Vct1	7 - 10 V	6 - 8 V	4 - 6 V	4 - 6 V
Vf	5 - 7 V	5 - 7 V	5 - 7 V	5 - 7 V
Vr	2 - 3 V	2 - 3 V	2 - 3 V	2 - 3 V
J201-1	2.5 - 4 V			
J201-3	6 - 8 V	6 - 8 V	6 - 8 V	6 - 8 V
J201-6	13.4 V	13.4 V	13.4 V	13.4 V

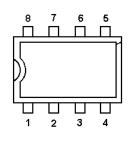
RATED POWER FOR MASTR III VHF BASE STATION

STANDARD	WITH	WITH	WITH DUPLEXER
	DUPLEXER	ISOLATOR	AND ISOLATOR
110W	75W	95W	70W

PARTS LIST IC DATA LBI-38531

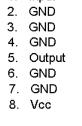


U100 19A705532P2 **VOLTAGE REGULATOR**

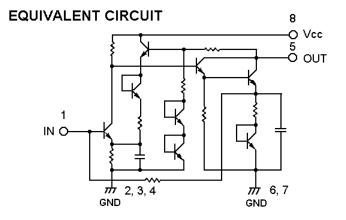


4. GND 5. Output

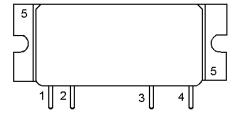
1. Input



CONNECTIONS



U101 344A3221P1 **MMIC AMPLIFIER**



- 1. P in
- 2. Vccı 1ST STAGE
- 3. Vcc FINAL
- 4. Pout
- 5. FIN GROUND

U102 19A70532P1 PA AMPLIFIER MODULE

110 WATT POWER AMPLIFIER 190902797G1 ISSUE 1

SYMBOL	GE PART NO.	DESCRIPTION
		ASSEMBLIES
Al		POWER AMPLIFIER BOARD 19D902794G1
		CAPACITORS
C100 and C101	19A702052P5	Ceramic: 1000 pF ±10%, 50 VDCW.
C103	19A702052P5	Ceramic: 1000 pF 210%, 50 VDCW.
C104 and C105	19A705108P120	Mica chip: 1000 pF, ±5%, 100 VDCW.
C106	19A705205P7	Tantalum: 10 uF, 25 VDCW; sim to Sprague 293D.
C109	19A705205F7	Tantalum: 10 uF, 25 VDCW; sim to Sprague 293D.
C110	1987051089120	Mics chip: 1000 pF. ±5%, 100 VDCW.
C111 and C112	19A705205P7	Tantalum: 10 uf, 25 VDCN; sim to Sprague 293D.
C114	19A705108P19	Mica: 18 pF ± 5%, 500 VDCW.
C115	19A705108P40	Mica chip: 91 pF, ±5%.
C116 and C117	19A705108P95	Capacitor, Mica Chip: 200pF ± 5%, 100 VDCW, temp coef 0 + 50 PPM.
C119	19A705108F22	Mica: 24 pf ± 5%, 500 VDCW.
C123	19A705108P22	Mica: 24 pF ± 5%, 500 VDCN.
C124	19A705108P30	Mica: 51 pf ± 5%, 500 VDCW.
C125	19A705108P35	Mica: 82 pF ±5%, 500 VDCW, temp coef 0 +50 PFM/*C.
C126	19A705108P30	Mica: 51 pF ± 5%, 500 VDCW.
C128 thru C130	19A705108P35	Mica: 82 pF ±5%, 500 VDCW, temp coef 0 +50 PPM/°C.
C131 and C132	344A3126P41	Porcelian: 130 pP ±5%, 300 VDCW,
C133 and C134	19A705108P120	Mica chip: 1000 pF, ±5%, 100 VDCW.
C135 and C136	344A3126P41	Porcelian: 130 pF ±5%, 300 VDCW.
C137 and C138	19A705108P120	Mica chip: 1000 pF, 25%, 100 VDCM,
C139	19A705108P33	Mica chip: 68 pf, 15%, 100 VDCW.
C140 and C141	19A705108P120	Nica chip: 1000 pF, ±5%, 100 VDCM.
C145	19A705108P25	Mica Chip: 33 pF 15%, 500 VDCR, temp coef 0 + 50 PPM/°C.
C147	19A705108P120	Hica chip: 1000 pr, ±5%, 100 VDCW.
C148	19A705108P36	Capacitor, Mica Chip: 91pF ± 5%, 500 VDCW, temp coef 0 + 50 PPW.
C152 and C153	19A705108P35	Mica: 82 pF 15%, 500 VDCW, temp coef 0 +50 PPM/'C.
C160 and C161	192705108P30	Mica: 51 pF ±5%, 500 VDCN, temp coef 0 +50 PPM/°C.
C164 and C165	19A705108P22	Mica: 24 pF ±5%, 500 VDCM, temp coef 0 +50 PPK/*C.
C166 and C167	. 19A705108P27	Mica Chip: 39 pF ±5%, 500 VDCN, temp coef 0 + 50 PFM/°C.
C168 and C169	19A705108P120	Hica chip: 1000 pF, ±5%, 100 VDCW.

SYMBOL	GE PART NO.	DESCRIPTION
C170 and C171	19A705205P7	Tantalum: 10 uF, 25 VDCW; sim to Sprague 293D.
C201	198702061941	Ceramic: 39 pF ± 5%, 50 VDCW, temp coef 0 ± 30 PPM.
C202 and C203	198702052926	Ceramic: 0.1 uF ± 10%, 50 VDCW.
G204	19A702061P41	Ceramic: 39 pF ± 5%, 50 VDCW, temp coef 0 ± 30 PPM.
C205 thru C207	19870205225	Ceramic: 1000 pF ±104, 50 VDCW.
C208	198702052P26	Ceramic: 0.1 uF ± 10%, 50 VDCW.
C209	19A702052P5	Ceramic: 1000 pF ±10%, 50 VDCW.
C213	19A702052P26	Ceramic: 0.1 uP ± 10%, 50 VDCW.
G225	19A702052P24	Ceramic: 0.068 uF ± 10%, 50 VDCW.
C263	19A702052PS	Ceramic: 1000 pF ±10%, 50 VDCW.
C266	19A702052P5	Ceramic: 1000 pF ±10%, 50 VDCW,
C270	19A702052P5	Ceramic: 1000 pF ±10%, 50 VDCM.
C272 and C273	19A702052P5	Ceramic: 1000 pF ±10%, 50 VDCM.
	}	
D201 and D202	198700047P3	19A702250P113
D203	19A700053P3	Silicon: 2 Diodes in Series, Common Cathode; sim to MBAV70L.
D205 and D206	19A700053F3	Silicon: 2 Diodes in Series, Common Cathode; sim to MBAV70L.
D209	19870004723	19A702250P113
D210	19A700083P102	Silicon: 5.1 Volt Zener; sim to BZX84-C5V1.
J101	198705512F1	Connector, RF SMB Series: sim to AMP No. 221111-1.
J103	19A702778P464	Threaded metalic spacer, swage type.
J201	19A704852P32	Printed wire, two part: 6 contacts, sim to Nolex 22-29-2061.
1		
1100	19870109101	Coil.
L101	19270109161	Coil. ·
L102	19A129569P1	Coil.
£103	19A701418P1	Coil.
L104	19A701420P5	Coil.
L105	198701091G1	Coil.
F106	19A129569P1	Coil.
L108	19A701418P1	Coil.
£115	19A701418P1	Coil.
L116	19A701420P5	Coil.
L117	19A701418P1	Coil.
L118	19R701420P5	Coil.
£119 and £120	19A129569P1	. coil.
Ll21 and Ll22	19A701420P5	Coil.
L123 and L124	19A701418P1	Coil.
L125 and L126	19R129360P4	Coil.
£160 and £161	344A3301P1	Ceil.

^{*}COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

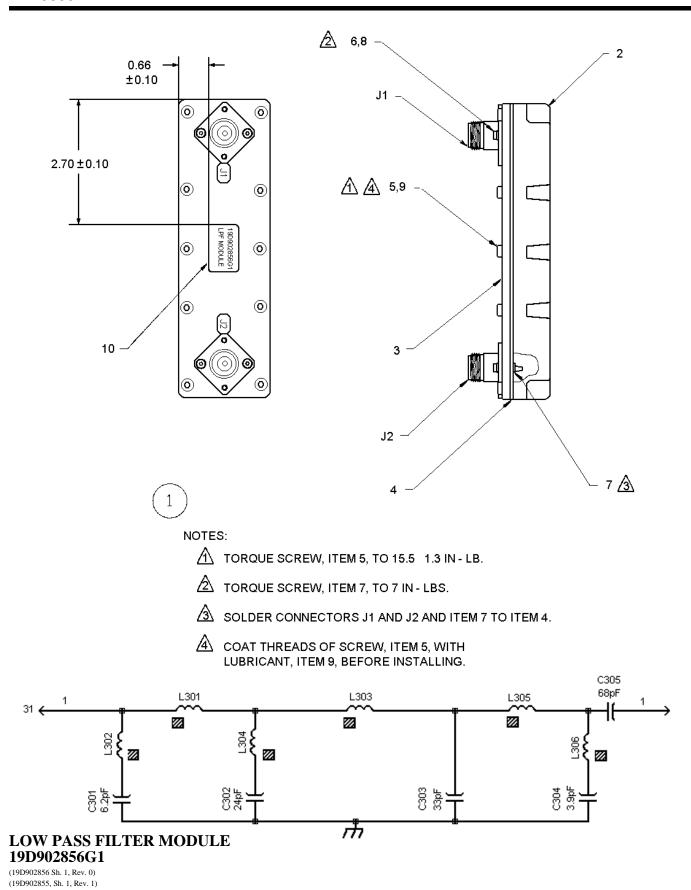
PARTS LIST

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
L203	19A700024P37	Coil, RF: 100 uH ± 10%.			
thru L205			J1		Part of W1.
			J104	7777145P5	Receptacle: sim to Amphenol 82-97.
Q201	19A700076P2	Silicon, MPN: sim to MMET3904, low profile.			
and 0202	138,000,002	Stitcon, NPR: Sim to MMBT3904, low profile.	0101	10217404024	TRANSISTORS
			Q101 Q102	19A134340P4	Silicon, NPN, VHF Amplifier: 45 w.
1	ļ	RESISTORS	and Q103	19814963291	Silicon, NPN, VHF Amplifier: 68 w., 12.5 volts.
RICC	198800607P270	Metal film: 27 ohms ±5%, 1/8 w.	Q203	19A700055P1	Silicon, PNP: Darlington; sim to TIP-125.
R101	1988006079330	Metal film: 33 ohms ±5%, 1/8 w.	•		orizon, into parriageon, oim to re-iri.
R102	198800607P270	Metal film: 27 ohms ±5%, 1/8 w,			RESISTORS
R103	19A700113P27 19B800607P331	Composition: 33 ohms ± 5%, 1/2 w.	R108	19A143832P4	Power: 50 ohms ±5%, 150 w.
R105	19B800607P331	Metal film: 330 chms ±5%, 1/8 w.	RILL	19A143832P4	Power: 50 ohms ±5%, 150 w.
RIO6	19B800607P331	Metal film: 10 ohms ±5%, 1/8 w. Metal film: 330 ohms ±5%, 1/8 w.			INTEGRATED CIRCUITS
R107	19A700113P5	Composition: 3.9 chms ± 5%, 1/2 w.	U100	19A705532P2	Integrated Circuit, Linear (Positive Voltage
R109	19A700112P15	Composition: 10 ohms : 5%, 1 w.	U102	19A705326P1	Regulator): sim to MC78T15CT. Power Amplifier Module: 145 to 175 MHz., sim to
R110	19A700112P13	Composition: 8.2 ohms 1 5%, 1 w.	3102	19870332021	Mitsubishi M57719
R112	198700112913	Composition: 8.2 ohms ± 5%, 1 w.	U103 and	344A3219P1	Coupler, hybrid: 130 to 180 MRz, amplitude balance ±0.25 dB; sim to Anaren Ro. 10262-3.
R201	198801486P1C1	Metal film: 100 ohms ±5%, 1/2 w.	U104	1	27.27 WG, 52m CO AMELER RG. 10262-3.
and R202				1	CABLES
R203	19B800607P103	Metal film: 10K ohms ±5%, 1/8 w.	WI	19B801529G4	RF Input Cable. Includes the following:
R204 R205	198800607P183	Metal film: 18K ohms ±5%, 1/8 w.		19B800560P2	RF Cable.
R205	19B800607P223	Netal film: 22K ohms ±5%, 1/8 w.		19A705512P3	Connector, RF SMB series: sim to AMP 228213-1.
R207	198702931P301	Netal film: 10K ohms ±5%, 1/8 w. Netal film: 10K ohms ±1%, 200 VDCW, 1/8 w.		19A115938P1	Connector, coamial: (BNC Series); sim to Amphenol 31-318.
and R208	134,01,311301	Actal IIIm: Tok bams fle, 200 VDCW, 1/8 V.			Amphenol 31-318.
R209	19A705813P2	Thermistor: sim to AL03006-58.2K-97-G100.	W4	198801695G11	Power Cable. Includes the following:
R210	19B800607P472	Hetal film: 4.7% ohms ±5%, 1/8 w.		19B209268P115	Solderless terminal.
and R211				19B209260P11	Solderless terminal.
R212 and	19A702931P301	Metal film: 10K ohms ±1%, 200 VDCW, 1/8 w.	İ	19A115959P2	Wire, stranded,
R213				19A701503P2 19A701503P10	Cable: battery, red.
R214 and	19B800607P103	Metal film: 10K ohms ±5%, 1/8 w.		198209268P116	Cable: battery, black. Solderless terminal.
R215			W10	19B801695G3	Power cable: W12-R.
R216	19B800607P102	Metal film: 1K ohma ±5%, 1/8 w.	W11	19880169564	Power cable: W12-BK.
R217	19A700109P5	Variable, cermet: 10K ohms : 20%, 1/4 w.	W13	198801739P1	Power Control cable.
R218 and R219	1988014867101	Metal film: 100 ohms ±5%, 1/2 w.		Ì	
R220	19A702931P333	Maked \$13-4 03 FW at 415 con upon 3 to	2		
R221	1987029318293	Metal film: 21.5K chums ±1%, 200 VDCW, 1/8 w. Metal film: 9090 chums ±1%, 200 VDCW, 1/8 w.	5	19D902420P6 19A702381P510	Heat sink assembly.
R223	19B800607P102	Metal film: 1K ohms ±5%, 1/8 w.	*	198/023817510	Screw, thread forming: TORX DRIVE No. M3.5 - 0.6 x 10.
R224	19B800607P103	Metal film: 10K ohms ±5%, 1/8 w.	6	7139898P3	Nut, hex, brass: No. 1/4-28.
R226	19B800607P103	Metal film: 10K ohms ±5%, 1/B w.	11	19A702364P310	Machine screw, TORX Drive: No. M3-0.5 x 10.
and R227		, =,-	16	19A700136P7	Insulated sleeving.
R228	198800607P102	Metal film: 1K ohms ±5%, 1/8 w.	21,	19A701863P27	Clip, loop.
R229	198800607P103	Metal film: 10K ohms ±5%, 1/8 w.	22	198701312P5	Platwasher: M3.5.
and R230			28	19A702364P316	Machine Screw: Pan Read, Steel.
R233	198800607P103	Metal film: 10K ohms ±5%, 1/8 w.	29 30	19A700034P4	Nut, hex: No. M3 x 0.5MM,
R235	198800607P103	Metal film: 10K ohms ±5%, 1/8 w.	35	19A700033P5	Lock washer, external tooth: No. 3. Insulator Plate, To-220.
1		INTEGRATED CIRCUITS	36	19A700068P1	Insulator Plate, 70-220. Insulator, bushing.
U101	344A3221P1	Linear: MMIC Amplifier; sim to NEC UPC1677C.	37	19A134455P3	Flatwasher.
U201	19A701789P4	Linear: Quad Op Amp; sim to LM224D.	38	19880165963	Cover (see separate parts list below).
	ļ		41	19A700033P6	Lockwasher, external tooth, M3.5.
C1	19A116708P2	Feedthru.	45	N405P5B6	Lockwasher.
"*		reedint 4.	46	19A701312P4	Flatwasher: 3.2 ID.
			so	198702381P408	Tap screw, TORK Drive, M3-0.5 x 8.
			51	19A705106P1	Resistor Spacer.

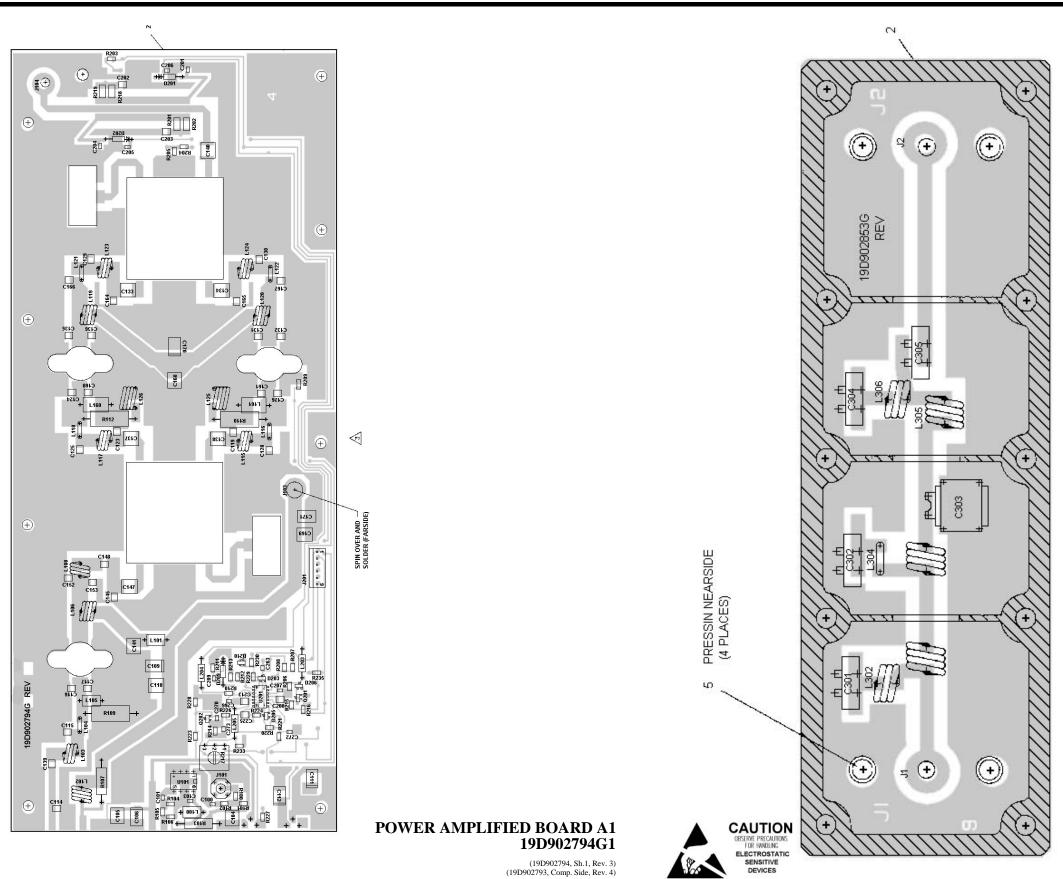
SYMBOL	GE PART NO.	DESCRIPTION	
		COVER 198801659G3	
2	19D902421P1	Power Amplifier Cover.	ł
4	19 3 702381P522	Screw, thread forming:	
5	19A701365P4	Washer.	
11	19A149969P3	Shield.	-
13	5493477P9	Axial fan.	i
14	5493477P10 N80P13028B6	Grille.	
15 16	M210P21B6	Machine screw. Machine nut.	1
17	198701312P5	Flatwasher: M3.5.	
18	19A701863P10	Clip, loop.	İ
20	198702364P410	Machine screw.	
21	19A700041P28	Shell.	
22	19A700041P26	Contact: sim to Molex 08-50-0113.	
24	N405P37B6	Lock washer.	
25	L401P23B6	Split washer.	
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LOW PASS FILTER MODULE 19D902856G1 ISSUE 1

SYMBOL	GE PART NO.	DESCRIPTION
		jacks
Jl and J2	7777145P5	Receptacle: sim to Amphenol 82-97.
		MISCELLANEOUS
2	19D903063P1	Casting.
3	190903064P1	Casting.
4	19D902853G1	High Band Filter Board. See separate parts list
5	19A702381P513	Screw, thread forming: TORX, No. M3.5 - 0.6 X 13.
6	19A702364P210	Machine screw, metric: M2.545 x 10.
7	19A134455P3	Flatwasher.
8	19A700032P3	Lockwasher, tooth, steel, metric: 2.5.
10	19B235310P1	Nameplate.
		HIGH BAND FILTER BOARD 19D902853G1
C301	19A116679P6R2D	6.2 pF.
C302	19A116679P24G	24 pF.
C303	19A116795P33G	33 pF.
C304	19A116679P3R9D	3.9 pF.
C305	19A116679P68J	68 pF.
L301	19A129569P1	Coil.
L302	19A701418F1	coil.
L303	19A129569P1	coil.
L304	19A701420P5	Coil.
L305	19A129569P1	Coil.
L306	19A701418P1	Coil.
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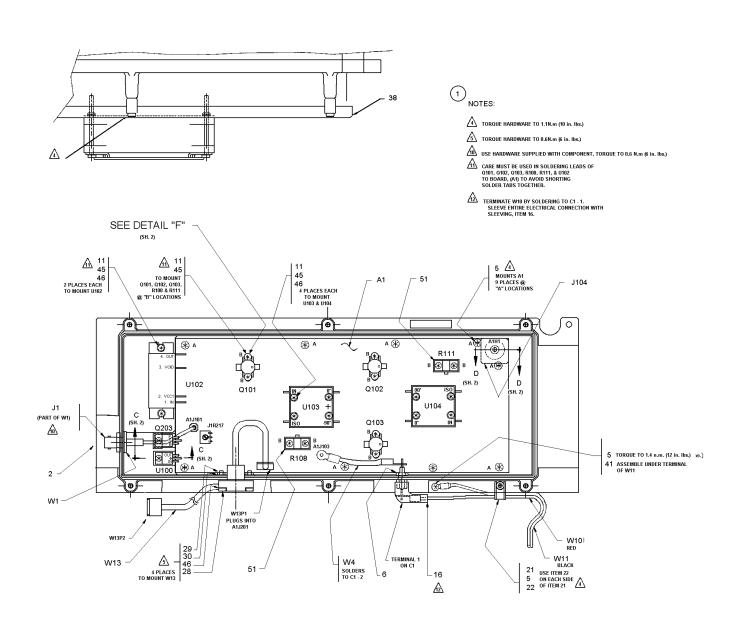


OUTLINE DIAGRAMS LBI-38531



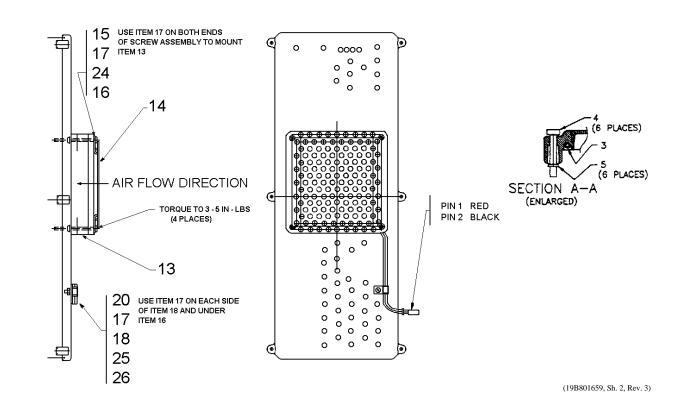
LOW PASS FILTER MODULE 19D902856G1

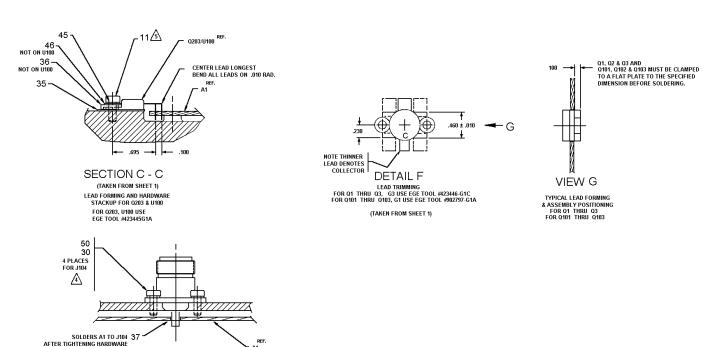
(19D902853, Sh.1, Rev. 2) (19D902854, Comp. Side, Rev. 9) LBI-38531 ASSEMBLY DIAGRAM



POWER AMPLIFIER ASSEMBLY 19D902797G1

(19D902797, Sh. 1, Rev. 6)





SECTION D - D

(TAKEN FROM SHEET 1)

POWER AMPLIFIER ASSEMBLY 19D902797G1

(19D902797, Sh. 2, Rev. 6)

SCHEMATIC DIAGRAM LBI-38531

